

isc P-Channel MOSFET Transistor

IRF5210,IIRF5210

• FEATURES

- Static drain-source on-resistance: $R_{DS}(on) \leq 0.06\Omega$
- Enhancement mode:
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

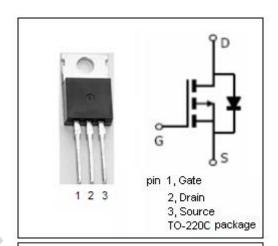
 Combine with the fast switching speed and ruggedized device design, provide the designer with an extremely efficient and reliable device for use in a wide variety of applications.

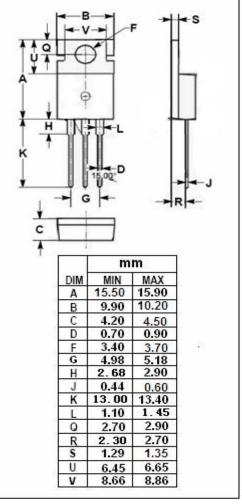
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	-100	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	-40	А	
I _{DM}	Drain Current-Single Pulsed	-140	А	
P_D	Total Dissipation @T _C =25℃	200	W	
Tj	Max. Operating Junction Temperature	175	$^{\circ}$	
T _{stg}	Storage Temperature	-55~175	$^{\circ}$ C	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	0.75	°C/W	
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W	





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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = -250 μ A	-100			V
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS; I _D = -250 μ A	-2.0		-4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V; I _D = -24A			0.06	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = -100V; V _{GS} = 0V			-25	μА
V _{SD}	Diode forward voltage	Is= -21A; V _{GS} = 0V			-1.6	V

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